SPICE Model Parameters

Copy this code from the SPICE model into a SPICE software program for simulation of the 1N8026-GA.

```
*     MODEL OF GeneSiC Semiconductor Inc.
*
*     $Revision:   1.0           $
*     $Date:   05-SEP-2013       $
*
*     GeneSiC Semiconductor Inc.
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*     Dulles, VA 20166
*
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*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of 1N8026-GA SPICE Model
*
.SUBCKT 1N8026 ANODE KATHODE
R1 ANODE INT R=((TEMP-24)*0.0021); Temperature Dependant Resistor
D1 INT KATHODE 1N8026_25C; Call the 25C Diode Model
D2 ANODE KATHODE 1N8026_PIN; Call the PiN Diode Model
.MODEL 1N8026_25C D
+ IS       4.45E-15        RS         0.206
+ N        1.18144         IKF        112.92
+ EG       1.2             XTI        3
+ CJO      3.00E-10        VJ         0.419
+ M        1.6             FC         0.5
+ TT       1.00E-10        BV         1200
+ IBV      1.00E-03        VPK        1200
+ IAVE     5               TYPE       SiC_Schottky
+ MFG      GeneSiC_Semiconductor
.MODEL 1N8026_PIN D
+ IS       2.93E-12        RS         0.35326
+ N        4.6113          IKF        0.0043236
+ EG       3.23            XTI        60
+ FC       0.5             TT         0
+ BV       1200            IBV        1.00E-03
+ VPK      1200            IAVE       2.5
+ TYPE     SiC_PiN
.ENDS
*
* End of 1N8026-GA SPICE Model
```